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MT 1259P



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Quality • Performance • Service

MT 4067P

(Micron 1 MEG PIN COMPATIBLE DRAM Family)

136

MT1259-P MT4067-P 262,144 x 1 BIT DYNAMIC RAM 65,536 x 4 BIT DYNAMIC RAM

FEATURES

- 256K × 1 and 64K × 4 DRAM's in Industry Standard 1 MEG
- Available in DIP, ZIP and SOJ packages.
- Compatible with 1 MEG DRAM refresh modes.
- Allows up-grade to 1 MEG DRAM's with no PC Board changes.

MARKING **OPTIONS** ×1. ×4 Timing -10100ns access 120ns access -12-15 150ns access Packages Р Plastic DIP Ceramic DIP CP ZP Plastic ZIP DJP Plastic SOJ

Order Example:
 256K x 1, 120ns access in plastic ZIP = MTI259ZP-12

The MT1259P/MT4067P are randomly accessed solid-state memories containing 262,144 bits organized in a ×1 or ×4 configuration. These devices are assembled in 1 MEG DRAM packages and conform to 1 MEG pin outs with the exception of address A9 which is a no connect (A8 on 256K × 4). This allows PC Board layout that is compatible with both 256K and 1 MEG DRAM's.

Care must be taken when specifying \overline{RAS} only refresh. 256K DRAM's use 256 cycle refresh distributed across 4ms while 1 MEG DRAM's use 512 cycle refresh distributed across 8 ms. Because of chip layout constraints some address scrambling was necessary to achieve the 1MEG x 1 pin out compatibility. It is necessary therefore, for the 512 cycle/8ms \overline{RAS} only refresh address (AO-A8) specification be satisfied for proper operation of the 256K X 1 part. This also insures proper operation of 1MEG DRAMs used in the same PC Board. No special considerations are required if \overline{CAS} before \overline{RAS} or Hidden Refresh cycles are employed.

The MT1259P/MT4067P is manufactured and quality controlled in Micron's modern Boise, Idaho USA facility. Refer to the MT1259P/MT4067P data sheet for all electrical specifications. Each unit receives accelerated burn-in and several hours of AMBYX™ system level-testing prior to final test and shipment.

PIN ASSIGNMENT (TOP VIEW)

18 Pin DIP		20 Pin DIP			
Din □•1	18 □ Vss	DQ1 🗗	20 🗆 Vss		
WE 2	17 🗀 Dout	DQ2 □ 2	19 🔁 DQ4		
RAS□3	16 □ CAS	WE □ 3	18 🔁 DQ3		
NC ☐ 4	15 Þ A9 ★	RAS ☐ 4	17 🗅 CAS		
A0 □ 5	14 🗅 A8	NC ☐ 5	16 🗅 ŌE		
A1 □ 6	13 🗆 A7	A 0 □ 6	15 🗅 A8**		
A2□ 7	12 🗆 A6	A1 □ 7	14 🏳 A7		
A3 □ 8	11 🗆 A5	A2□ 8	13 🖯 A6		
Vcc ☐ 9	10 🗅 A4	A 3 □ 9	12 🗅 A5		
L		Vcc □ 10	11 🗅 A4		

20 Pin SOJ			20 Pin SOJ		
Din 🗆	1	26 Vss	DQ1 d	1	26 □ Vss
WE C	2	25 Dout	DQ2	.2	25 DQ4
RAS [3	24 🗅 CAS	WE d	3	24 🗀 DQ3
NC 🗆	4	23 🏻 NC	RAS 🗆	4	23 🗆 CAS
NC 🗆	5	22 □ A9*	NC 🗆	5	22 D OE
;					
A0 🗆	9	18 🗅 A8	A0 🗆	9	18 🗆 A8**
A1 🗆	10	17 🗅 A7	A1 🗆	10	17 🗅 A7
A2 🗆	11	16 🗅 A6	A2 🗆	11	16 🗅 A6
A 3 🗆	12	15 🗅 A5	A3 🗆	12	15 🗅 A5
Vcc □	13	14 A4	Vcc 🗆	13	14 A4

20 Pin ZIP			2	20 Pin ZIP			
*A9	[]] 1	2 []]	CAS	ŌE	[]] 1	2 []]	CAS
Dout	EE33	4 []]	Vss		[]]3	4 []]	DQ4
Din	[]]5	6 📖	WE		[]]5	6 []]	DQ1
RAS	[]] 7 []] 9	8 📖	NC		[]] 7 []] 9	8 []]]	WE
AO	[]]11	10	NC	· · · · -	EEE 11	10[]]	NC
A2	[]]13	12[[]]	A 1		[]]]	12[[]]	A1
Vcc	[]]15	14[]]	A3	. —	£***15	14[]]	A3
A 5	CCC 17	16[[]]	A4	A5	[]]17	16[]	A4
A 7	E:::319	18[]]	A6	A7	[]]19	18[]]	A6
		20	A8			20[]]	A8 **

*No connect-used as A9 on 1 MEG x 1.
**No connect-used as A8 on 256K x 4.

Please contact the factory for technical, test and application assistance. Micron can also furnish the representative and distributor nearest you. Micron's QUALITY ASSURED policy is to offer prompt, accurate and courteous service while assuring quality and reliability. The success of our memory business depends on the success of your application.

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